TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSVII)

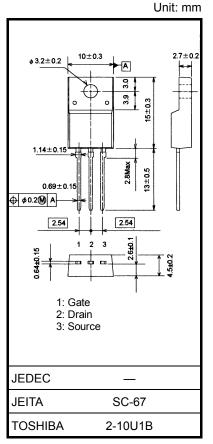
# **TK10A60D**

#### **Switching Regulator Applications**

- Low drain-source ON-resistance:  $R_{DS}$  (ON) = 0.62  $\Omega$  (typ.)
- High forward transfer admittance: |Y<sub>fs</sub>| = 6.0 S (typ.)
- Low leakage current:  $I_{DSS} = 10 \mu A (V_{DS} = 600 V)$
- Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

### Absolute Maximum Ratings (Ta = 25°C)

| Characteristics                                      |                              | Symbol           | Rating     | Unit |  |
|--|------------------------------|------------------|------------|------|--|
| Drain-source voltage                                 |                              | $V_{DSS}$        | 600        | V    |  |
| Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ ) |                              | $V_{DGR}$        | 600        | V    |  |
| Gate-source voltage                                  |                              | V <sub>GSS</sub> | ±30        | V    |  |
| Drain current  | DC (Note 1)                  | I <sub>D</sub>   | 10         |      |  |
|  | Pulse (t = 1 ms)<br>(Note 1) | I <sub>DP</sub>  | 40         | Α    |  |
| Drain power dissipati                                | on (Tc = 25°C)               | P <sub>D</sub>   | 45         | W    |  |
| Single pulse avalanche energy (Note 2)               |                              | E <sub>AS</sub>  | 363        | mJ   |  |
| Avalanche current                                    |                              | I <sub>AR</sub>  | 10         | Α    |  |
| Repetitive avalanche energy (Note 3)                 |                              | E <sub>AR</sub>  | 4.5        | mJ   |  |
| Channel temperature                                  |                              | T <sub>ch</sub>  | 150        | °C   |  |
| Storage temperature range                            |                              | T <sub>stg</sub> | -55 to 150 | °C   |  |



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### **Thermal Characteristics**

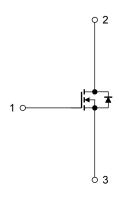
| Characteristics                        | Symbol                 | Max  | Unit |
|--|------------------------|------|------|
| Thermal resistance, channel to case    | R <sub>th (ch-c)</sub> | 2.78 | °C/W |
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 62.5 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 6.36 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 10 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.



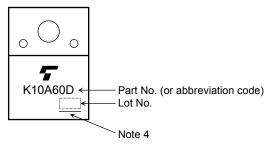
#### **Electrical Characteristics (Ta = 25°C)**

| Char                           | acteristics   | Symbol               | Test Condition   | Min | Тур. | Max  | Unit  |
|--------------------------------|---------------|----------------------|--|-----|------|------|-------|
| Gate leakage current           |               | I <sub>GSS</sub>     | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$  | _   | _    | ±1   | μΑ    |
| Drain cut-off current          |               | I <sub>DSS</sub>     | V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V   | _   | _    | 10   | μΑ    |
| Drain-source breakdown voltage |               | V (BR) DSS           | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V  | 600 | _    |      | ٧     |
| Gate threshold v               | oltage        | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA  | 2.0 | _    | 4.0  | ٧     |
| Drain-source ON                | -resistance   | R <sub>DS (ON)</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A   |     | 0.62 | 0.75 | Ω     |
| Forward transfer               | admittance    | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 5 A   | 1.5 | 6.0  |      | S     |
| Input capacitance              |               | C <sub>iss</sub>     |  |     | 1350 |      | pF    |
| Reverse transfer capacitance   |               | C <sub>rss</sub>     | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz   |     | 6    |      |       |
| Output capacitance             |               | Coss                 |  | _   | 135  | _    |       |
| Switching time                 | Rise time     | t <sub>r</sub>       | $\begin{array}{c c} 10 \text{ V} & \text{I}_D = 5 \text{ A} & \text{V}_{\text{OUT}} \\ \hline \text{VGS} & \text{V} & \text{V}_{\text{DD}} \approx 200 \text{ V} \\ \hline \text{Duty} \leq 1\%, \ t_{\text{W}} = 10  \mu\text{s} \end{array}$ | _   | 22   | _    |       |
|                                | Turn-on time  | t <sub>on</sub>      |  | _   | 55   | _    | 20    |
|                                | Fall time     | t <sub>f</sub>       |  |     | 15   |      | ns ns |
|                                | Turn-off time | t <sub>off</sub>     |  |     | 100  |      |       |
| Total gate charge              |               | Qg                   |  | _   | 25   | _    |       |
| Gate-source charge             |               | Q <sub>gs</sub>      | $V_{DD} \simeq 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$   | _   | 16   | _    | nC    |
| Gate-drain charge              |               | Q <sub>gd</sub>      |  | _   | 9    |      |       |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol           | Test Condition                                 | Min | Тур. | Max  | Unit |
|---|------------------|--|-----|------|------|------|
| Continuous drain reverse current (Note 1) | $I_{DR}$         | _  | _   | _    | 10   | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | _  | _   | _    | 40   | Α    |
| Forward voltage (diode)                   | $V_{DSF}$        | I <sub>DR</sub> = 10 A, V <sub>GS</sub> = 0 V  | _   | _    | -1.7 | V    |
| Reverse recovery time                     | t <sub>rr</sub>  | $I_{DR} = 10 \text{ A}, V_{GS} = 0 \text{ V},$ |     | 1300 |      | ns   |
| Reverse recovery charge                   | Q <sub>rr</sub>  | dl <sub>DR</sub> /dt = 100 A/μs                | _   | 12   | _    | μС   |

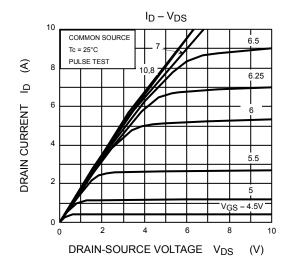
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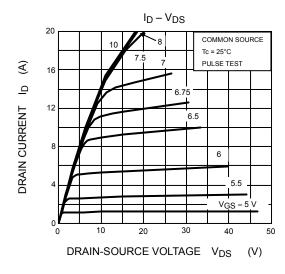


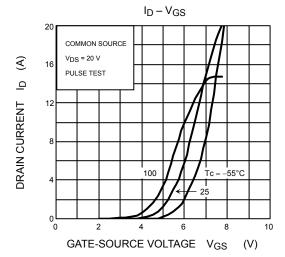
Note 4: A line under a Lot No. identifies the indication of product Labels.

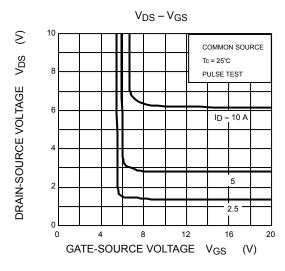
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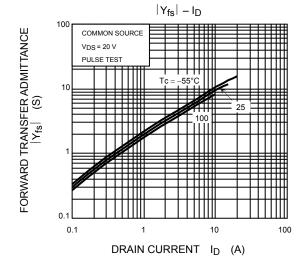
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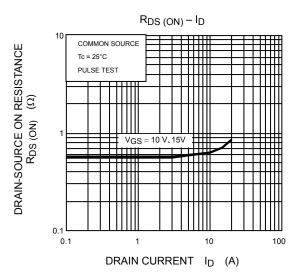


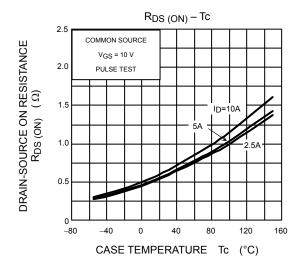


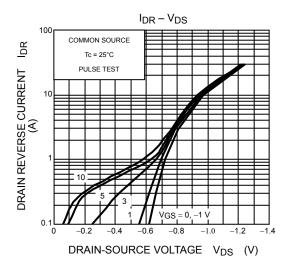


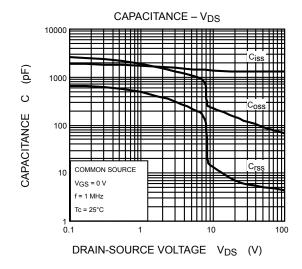


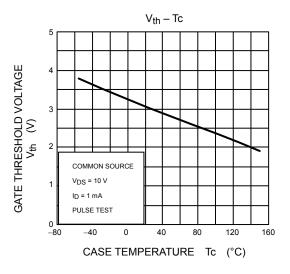


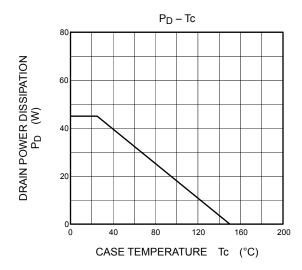


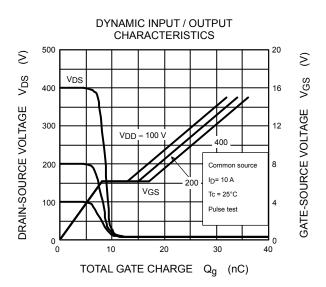


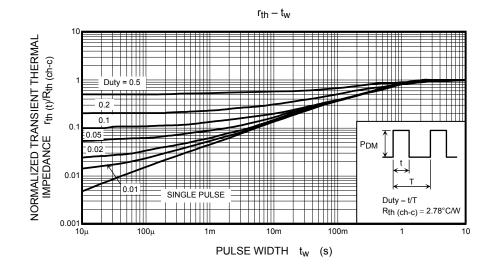


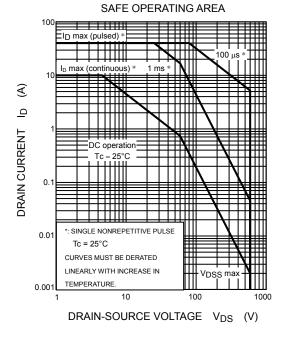


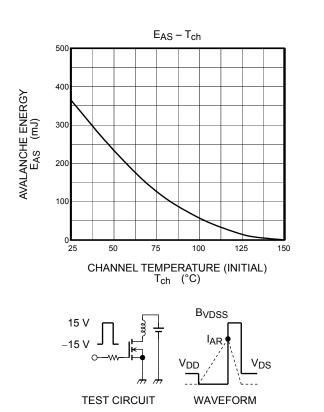












 $R_G=25\;\Omega$ 

 $V_{DD} = 90 \text{ V}, L = 6.36 \text{mH}$ 

 $E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$ 

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